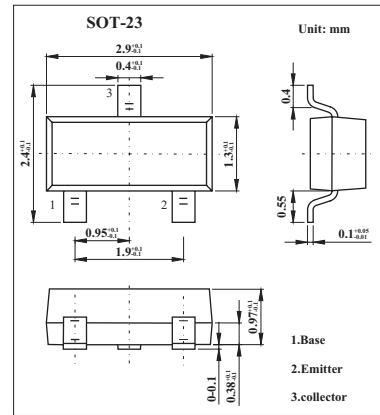


■ Features

- Low current (max. 25 mA).
- Low voltage (max. 40 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-40	V
Collector-emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-4	V
Collector current	I _c	-25	mA
Peak collector current	I _{CM}	-25	mA
Total power dissipation *	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	I _E = 0; V _{CB} = -30 V			-50	nA
Emitter cutoff current	I _{EBO}	I _C = 0; V _{EB} = -3 V			-100	nA
DC current gain	h _{FE}	I _C = -1 mA; V _{CE} = -10 V	50			
Base to emitter voltage	V _{BE}	I _C = -1 mA; V _{CE} = -10 V		750		mV
Feedback capacitance	C _{re}	I _C = -1 mA; V _{CB} = -10 V; f = 1 MHz		0.5		pF
Transition frequency	f _T	I _C = -1 mA; V _{CE} = -10 V; f = 100 MHz		325		MHz

■ Marking

Marking	LA
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